

MOSFETs Silicon Carbide N-Channel MOS

# TW031V65C

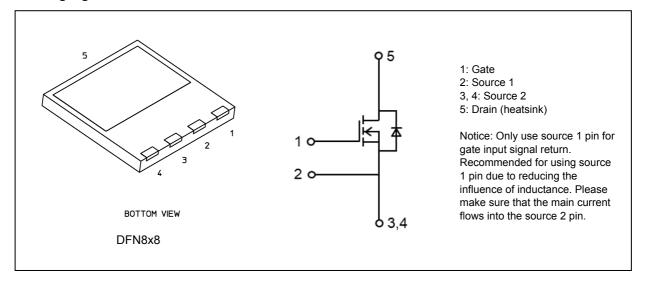
### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage:  $V_{DSF} = -1.35 \text{ V (typ.)}$
- (3) High voltage:  $V_{DSS} = 650 \text{ V}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 31 \text{ m}\Omega$  (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage:  $V_{th} = 3.0$  to 5.0 V ( $V_{DS} = 10$  V,  $I_D = 3$  mA)
- (6) Recommended gate source drive voltage:  $V_{GS\_on} = 18 \text{ V}$ ,  $V_{GS\_off} = 0 \text{ V}$
- (7) Enhancement mode.

### 3. Packaging and Internal Circuit





# 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

	Characteristics	Symbol	Rating	Unit	
Drain-source voltage			V <sub>DSS</sub>	650	V
Gate-source voltage			V <sub>GSS</sub>	+25/-10	
Drain current (DC)	( T <sub>c</sub> = 25 °C )	(Note 1)	I <sub>D</sub>	53	Α
Drain current (DC)	( T <sub>c</sub> = 100°C )	(Note 1)	I <sub>D</sub>	38	
Drain current (pulsed)	( T <sub>c</sub> = 25 °C )	(Note 1)	I <sub>DP</sub>	163	
Drain current (pulsed)	( T <sub>c</sub> = 100°C )	(Note 1)	I <sub>DP</sub>	122	]
Power dissipation	( T <sub>c</sub> = 25°C )		P <sub>D</sub>	156	W
Channel temperature			T <sub>ch</sub>	175	℃
Storage temperature	-		T <sub>stg</sub>	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	0.961	°C/W

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.



### 6. Electrical Characteristics

# 6.1. Static Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		$I_{GSS}$	V <sub>GS</sub> = +25/-10 V, V <sub>DS</sub> = 0 V	_	_	±0.1	μΑ
Drain cut-off current		I <sub>DSS</sub>	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V	_	7.0	100	
			T <sub>a</sub> = 150 °C, V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V	ı	37	ı	
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D$ = 4 mA, $V_{GS}$ = 0 V	650		_	V
Gate threshold voltage (N	Note 2)	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3 mA	3.0	_	5.0	
Drain-source on-resistance		R <sub>DS(ON)</sub>	V <sub>GS</sub> = 18 V, I <sub>D</sub> = 29 A	_	31	45	mΩ
			T <sub>a</sub> = 150 °C, V <sub>GS</sub> = 18 V, I <sub>D</sub> = 29 A	_	35	_	

Note 2: Please be sure to apply  $I_{GSS}$  ( $V_{GS}$  = 25 V) before the  $V_{th}$  test.



### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V,	_	2288	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 100 kHz	_	6.6	_	
Output capacitance	C <sub>oss</sub>	1	_	249	_	
Effective output capacitance (energy related)	C <sub>o(er)</sub>		_	288	_	
Effective output capacitance (time related)	C <sub>o(tr)</sub>		_	413	_	
Output charge	Q <sub>oss</sub>	]	_	165	_	nC
C <sub>oss</sub> stored energy	E <sub>oss</sub>	1	_	23	_	μJ
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz	_	2.1	_	Ω
Turn-on delay time	t <sub>d(on)</sub>	See Fig. 6.2.1	_	30	_	ns
Switching time (rise time)	t <sub>r</sub>	1	_	15	_	
Turn-off delay time	t <sub>d(off)</sub>	1	_	42	_	
Switching time (fall time)	t <sub>f</sub>	1	_	18	_	
Turn-on switching loss	E <sub>on</sub>			163		μJ
Turn-off switching loss	E <sub>off</sub>	]	_	100	_	

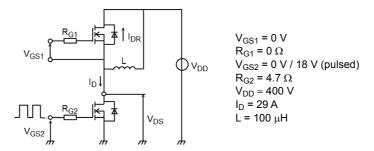


Fig. 6.2.1 Switching Time Test Circuit

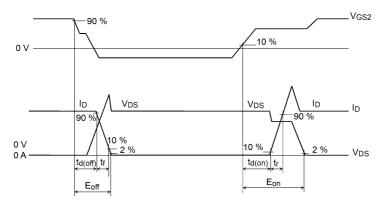


Fig. 6.2.2 Timing Diagrams



# 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)		$V_{DD} \approx 400 \text{ V}, V_{GS} = 18 \text{ V},$ $I_{D} = 29 \text{ A}$	_	65		nC
Gate-source charge 1	Q <sub>gs1</sub>			26		
Gate-drain charge	$Q_{gd}$		_	10	_	

# 6.4. Source $\cdot$ Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 3)	I <sub>DR</sub>	T <sub>c</sub> = 25 °C, V <sub>GS</sub> = -5 V	_	_	44	Α
			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = -5 V	_	_	29	
			T <sub>c</sub> = 25 °C, V <sub>GS</sub> = 18 V	_	_	53	
			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = 18 V	_	_	38	
Reverse drain current	(Note 3)	I <sub>DRP</sub>	T <sub>c</sub> = 25 °C, V <sub>GS</sub> = -5 V	_	_	163	
(pulsed)			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = -5 V	_	_	75	
			T <sub>c</sub> = 25 °C, V <sub>GS</sub> = 18 V	_	_	163	
			T <sub>c</sub> = 100 °C, V <sub>GS</sub> = 18 V	_	_	122	
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = 21 A, V <sub>GS</sub> = -5 V	_	-1.35	-1.80	V
			T <sub>a</sub> = 150 °C, I <sub>DR</sub> = 21 A, V <sub>GS</sub> = -5 V		-1.57		
Reverse recovery time		t <sub>rr</sub>	I <sub>DR</sub> = 19 A, V <sub>GS</sub> = 0 V,	_	55	_	ns
Reverse recovery charge	_	Q <sub>rr</sub>	$V_{DD} = 400 \text{ V}, -dI_{DR}/dt = 1000 \text{ A}/\mu\text{s}$	_	358		nC
Peak reverse recovery current		I <sub>rr</sub>		_	13	_	Α

Note 3: Ensure that the channel temperature does not exceed 175  $^{\circ}\text{C}$ .



### 7. Marking

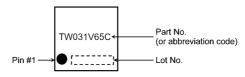


Fig. 7.1 Marking



### 8. Characteristics Curves (Note)

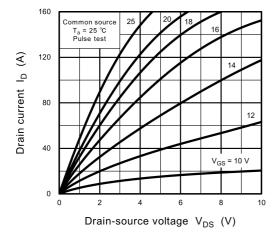


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

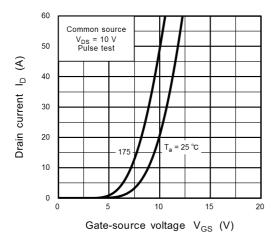


Fig. 8.3 ID - VGS

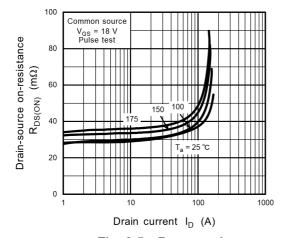


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

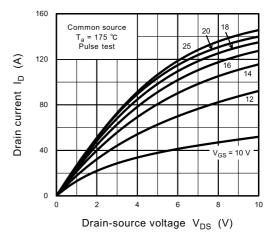


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

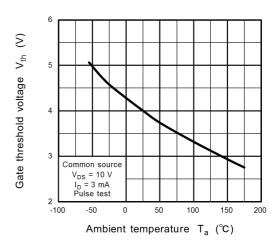


Fig. 8.4 V<sub>th</sub> - T<sub>a</sub>

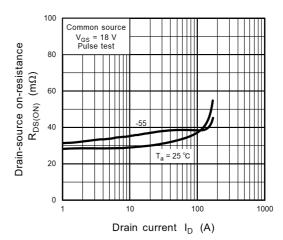


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>

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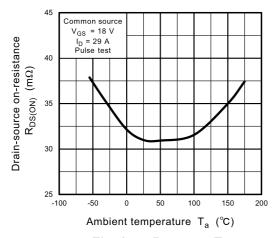


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>

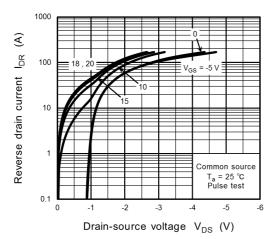


Fig. 8.9 IDR - VDS

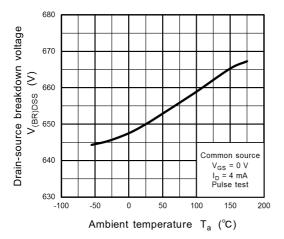


Fig. 8.11 V<sub>(BR)DSS</sub> - T<sub>a</sub>

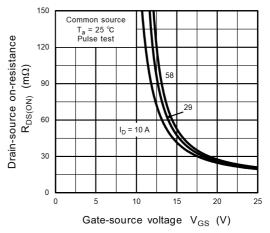


Fig. 8.8 R<sub>DS(ON)</sub> - V<sub>GS</sub>

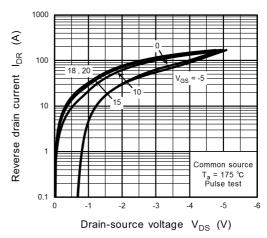


Fig. 8.10 I<sub>DR</sub> - V<sub>DS</sub>

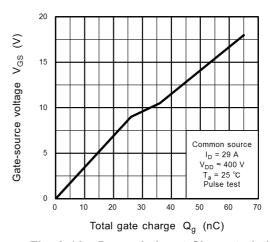


Fig. 8.12 Dynamic Input Characteristics



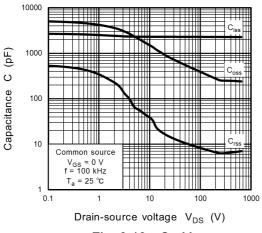


Fig. 8.13 C - V<sub>DS</sub>

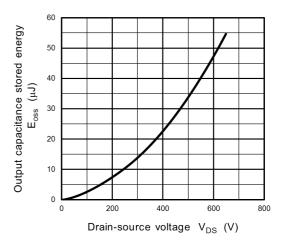


Fig. 8.14 Eoss - VDS

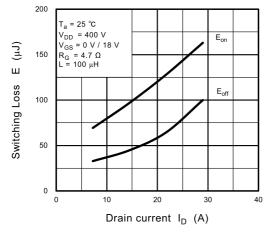


Fig. 8.15 E - I<sub>D</sub>

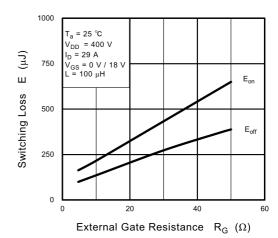


Fig. 8.16 E - R<sub>G</sub>

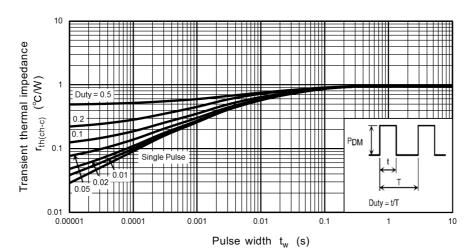
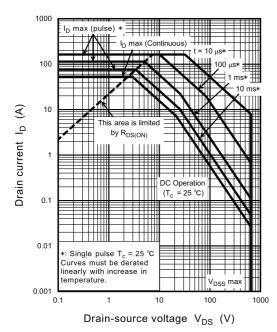


Fig. 8.17  $r_{th(ch-c)} - t_w$  (Guaranteed Maximum)





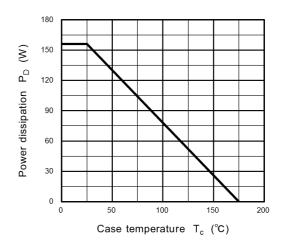


Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

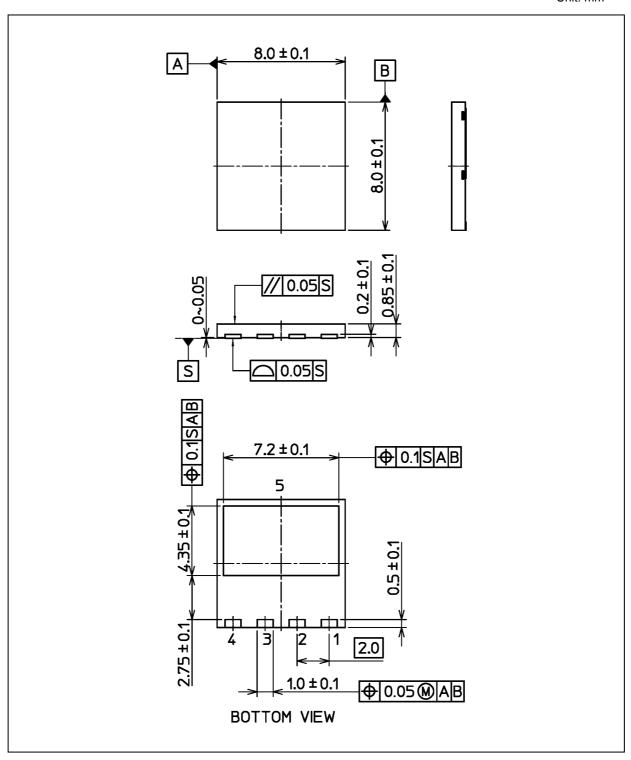
Fig. 8.19 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 0.175 g (typ.)

	Package Name(s)
TOSHIBA: 2-8T1A	
Nickname: DFN8x8	



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